

General Description

The WSD4062DN56 is the highest performance trench N-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The WSD4062DN56 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

Product Summery

BVDSS	RDSON	ID
40V	7.0mΩ	62A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Power Tool Application

DFN5X6-8L Pin Configuration



Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	±20	V
I₀@Tc=25℃	Continuous Drain Current, V _{GS} @ 10V	62	A
I _D @T _C =100℃	Γ _C =100°C Continuous Drain Current, V _{GS} @ 10V 29		
I _{DM}	I _{DM} Pulsed Drain Current ^a 60		A
EAS	Single Pulse Avalanche Energy ^b	42	mJ
I _{AS}	Avalanche Current 13		A
P _D @T _a =25℃	25°C Total Power Dissipation 2		W
T _{STG}	Storage Temperature Range -55 to 150		°C
TJ	T _J Operating Junction Temperature Range -55 to 150		

Thermal Data

Symbol	Symbol Parameter		Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹		60	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹		3.9	°C/W

Note a : Package is limited to 60A.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature Tj=25°C).

Absolute Maximum Ratings



Electrical Characteristics (T_J=25 ^(C), unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	40			V
$\triangle BV_{DSS} / \triangle T_J$	BV _{DSS} Temperature Coefficient	Reference to 25 $^\circ\!\mathrm{C}$, I_D=1mA		0.043		V/° C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =20A		7.0	10.5	mΩ
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V , I _D =15A		9.0	13.5	mΩ
V _{GS(th)}	Gate Threshold Voltage		1.5	1.8	2.5	V
$ riangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_{D}=250$ uA		-6.94		mV/℃
1	Drain-Source Leakage Current	$V_{\text{DS}}\text{=}48\text{V}$, $V_{\text{GS}}\text{=}0\text{V}$, $T_{\text{J}}\text{=}25^\circ\!\mathrm{C}$			2	
I _{DSS}	Dialit-Source Leakage Current	V_{DS} =48V , V_{GS} =0V , T_{J} =55 $^{\circ}\mathrm{C}$			10	uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance V _{DS} =5V , I _D =20A			33		S
R _g	Gate Resistance V _{DS} =0V , V _{GS} =0V , f=1MHz			1.1	2	Ω
Qg	Total Gate Charge (10V)			76	91	
Q _{gs}	Gate-Source Charge V _{DS} =20V , V _{GS} =10V , I _D =40A			12	14.4	nC
Q _{gd}	Gate-Drain Charge			15.5	18.6	
T _{d(on)}	Turn-On Delay Time			12	16	
Tr	Rise Time	V_{DD} =30V , V_{GEN} =10V , R_G =1 Ω ,		9	12	20
T _{d(off)}	Turn-Off Delay Time	I _D =1A ,RL=15Ω.		25	32	ns
T _f	Fall Time			6	9	
C _{iss}	Input Capacitance			1150		
C _{oss}	Output Capacitance	V _{DS} =20V , V _{GS} =0V , f=1MHz		140		pF
C _{rss}	Reverse Transfer Capacitance			90		

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			20	А
I _{SM}	Pulsed Source Current ^{2,6}				60	А
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =20A , TJ=25℃			1.3	V

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper,t<10sec .

2.The data tested by pulsed , pulse width $\,\leq\,$ 300us , duty cycle $\,\leq\,$ 2%

3. The EAS data shows Max. rating . The test condition is V_{DD} =25V, V_{GS} =10V, L=0.5mH, I_{AS} =13A

4.The power dissipation is limited by 150° C junction temperature

5. The Min. value is 100% EAS tested guarantee.

6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

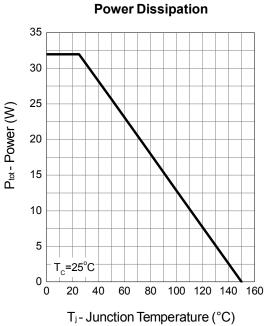
7.Package limitation current is 60A.



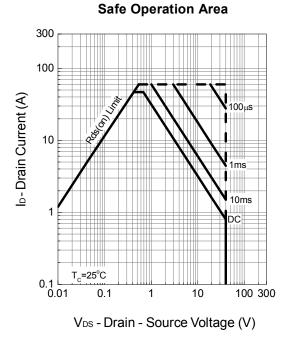
WSD4062DN56

N-Ch MOSFET

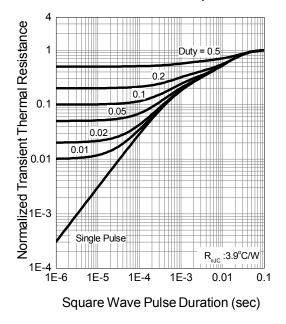
Typical Characteristics



T_j-Junction Temperature (°C)

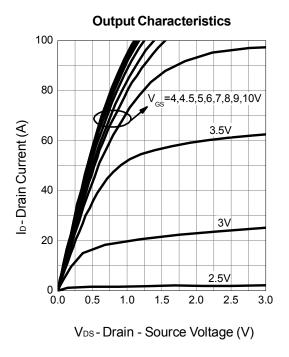


Thermal Transient Impedance



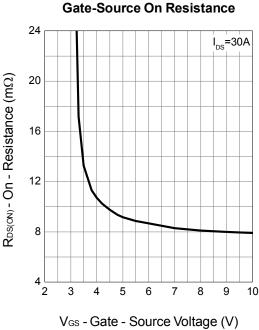


Typical Characteristics

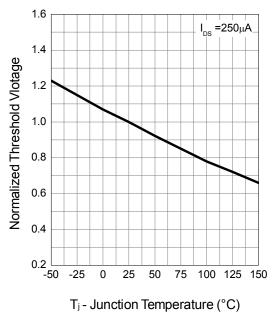


Drain-Source On Resistance 14 12 RDS(ON) - On - Resistance (mΩ) V_{GS}=4.5V 10 V_{GS}=10V 8 6 4 · 0 10 30 40 50 20 60

ID-Drain Current (A)





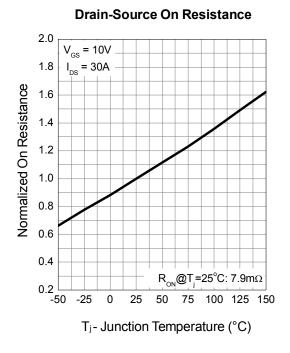


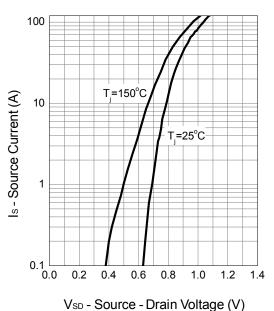
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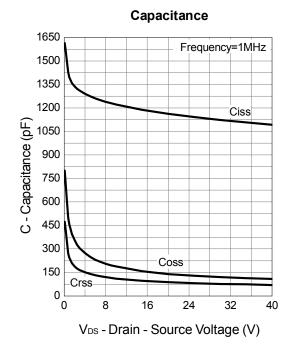
WSD4062DN56

Typical Characteristics

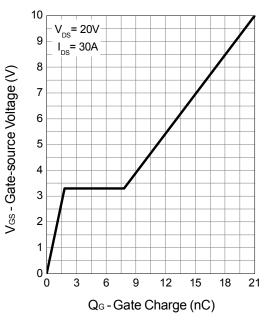




Source-Drain Diode Forward



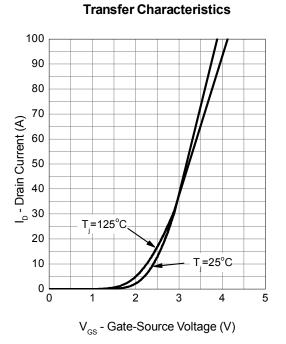








Typical Characteristics



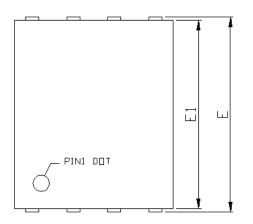
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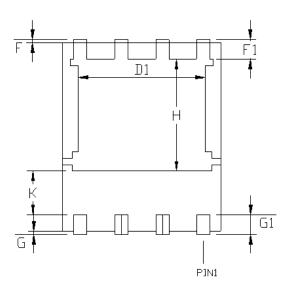


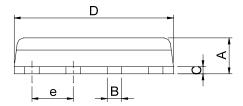
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N-Ch MOSFET

Package DFN5x6-8L

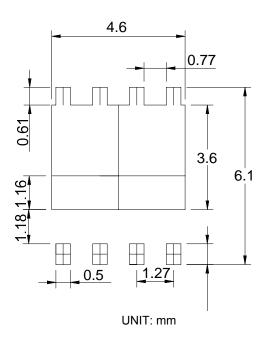






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SYMBOL	MILLIMETERS		INCHES		
l c	MIN.	MAX.	MIN.	MAX.	
А	0.90	1.20	0.035	0.047	
В	0.3	0.51	0.012	0.020	
С	0.19	0.25	0.007	0.010	
D	4.80	5.30	0.189	0.209	
D1	3.6	4.40	0.141	0.173	
E	5.90	6.20	0.232	0.244	
E1	5.50	5.80	0.217	0.228	
е	1.27	BSC	0.050 BSC		
F	0.05	0.30	0.002	0.012	
F1	0.35	0.75	0.014	0.030	
G	0.05	0.30	0.002	0.012	
G1	0.35	0.75	0.014	0.030	
Н	3.34	3.9	0.131	0.154	
к	0.762	-	0.03	-	

RECOMMENDED LAND PATTERN



Note : 1.Dimension D, D1 and E1 do not include mold flash or protrusions.

Mold flash or protrusions shall not exceed 10 mil.



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